


SANYO Semiconductors

DATA SHEET

SCH2809

MOSFET : P-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

General-Purpose Switching Device Applications

Features

- Composite type with a P-channel silicon MOSFET (SCH1305) and a Schottky barrier diode (SBS018) contained in one package facilitating high-density mounting.
- [MOSFET]
 - Low ON-resistance.
 - Ultrahigh-speed switching.
 - 1.8V drive.
- [SBD]
 - Short reverse recovery time.
 - Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-1.2	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-4.8	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V _{RSM}		15	V
Average Output Current	I _O		0.5	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	3	A
Junction Temperature	T _j		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : QJ

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

SCH2809

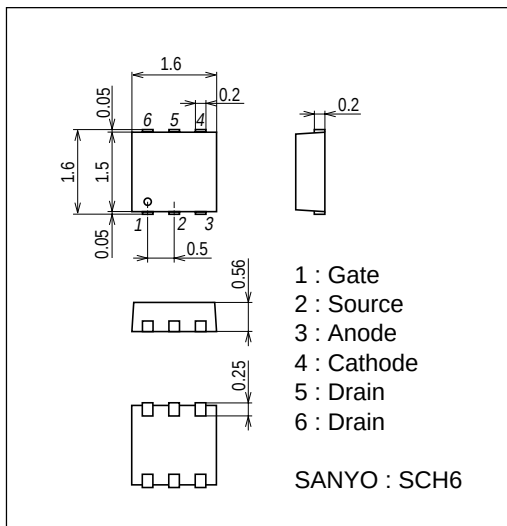
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12V, V_{GS}=0V$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-6V, I_D=-1mA$	-0.3		-1.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-6V, I_D=-0.8A$	1.08	1.8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-0.6A, V_{GS}=-4.5V$		235	310	$m\Omega$
	$R_{DS(on)2}$	$I_D=-0.3A, V_{GS}=-2.5V$		335	470	$m\Omega$
	$R_{DS(on)3}$	$I_D=-0.1A, V_{GS}=-1.8V$		445	670	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-6V, f=1MHz$		160		pF
Output Capacitance	C_{oss}	$V_{DS}=-6V, f=1MHz$		45		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-6V, f=1MHz$		35		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		45		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		29		ns
Fall Time	t_f	See specified Test Circuit.		30		ns
Total Gate Charge	Q_g	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-1.2A$		2.6		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-1.2A$		0.25		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-1.2A$		0.65		nC
Diode Forward Voltage	V_{SD}	$I_S=-1.2A, V_{GS}=0V$		-0.92	-1.5	V
[SBD]						
Reverse Voltage	V_R	$I_R=0.5mA$	15			V
Forward Voltage	V_F	$I_F=0.5A$		0.4	0.46	V
Reverse Current	I_R	$V_R=6V$			90	μA
Interterminal Capacitance	C	$V_R=10V, f=1MHz$		13		pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=100mA$, See specified Test Circuit.			10	ns

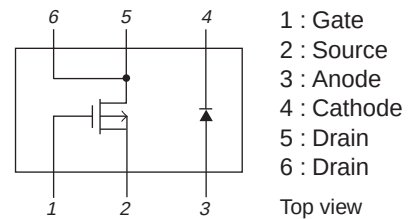
Package Dimensions

unit : mm

7028-003

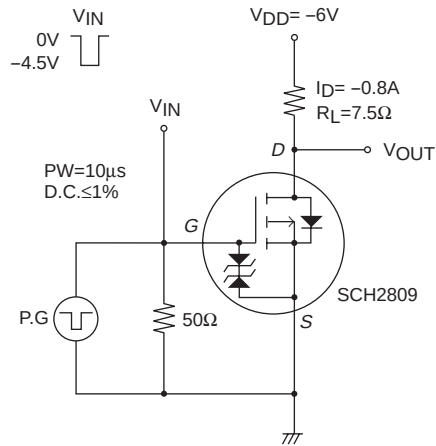


Electrical Connection



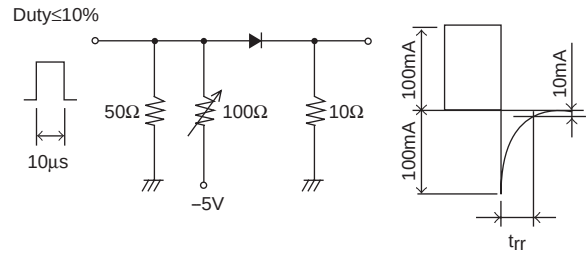
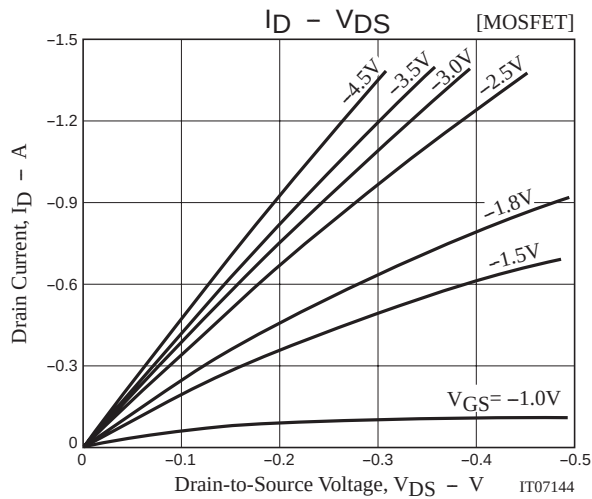
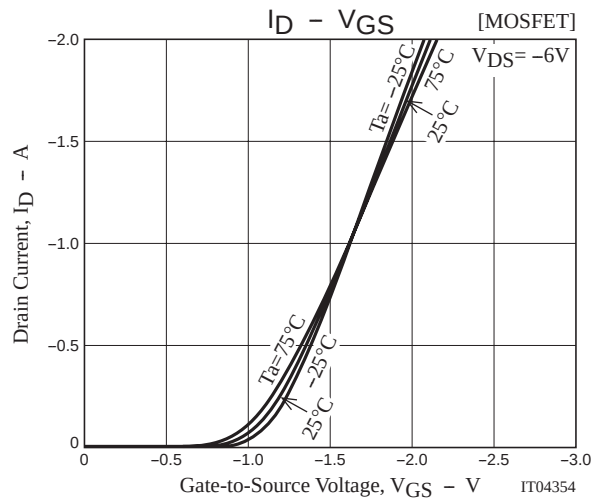
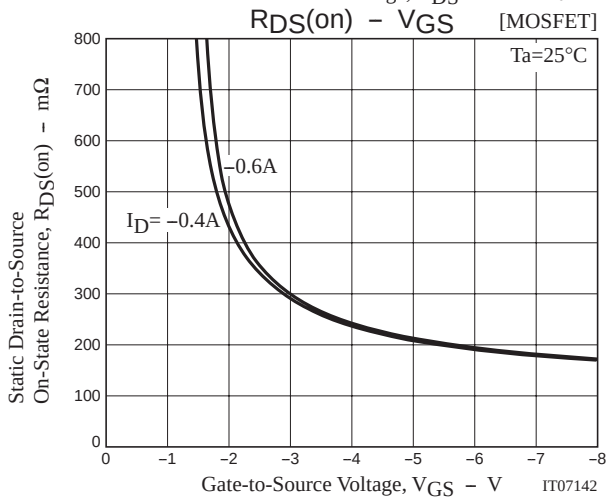
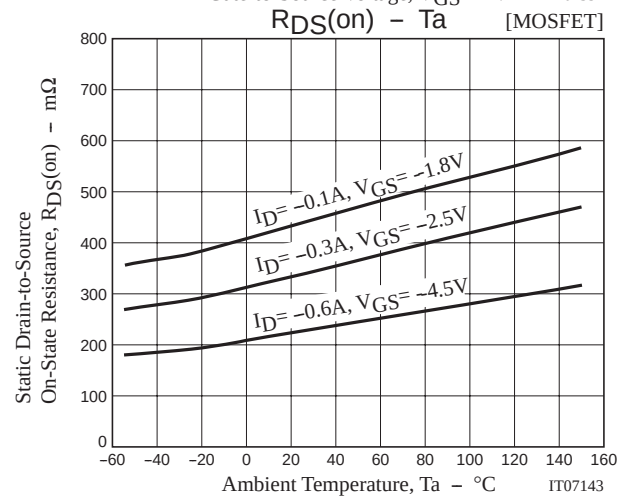
Switching Time Test Circuit

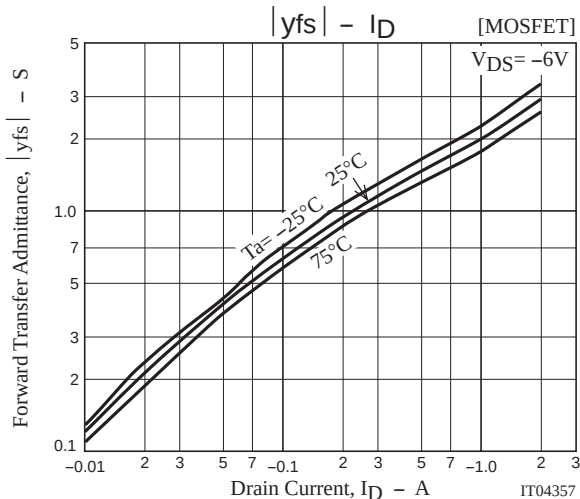
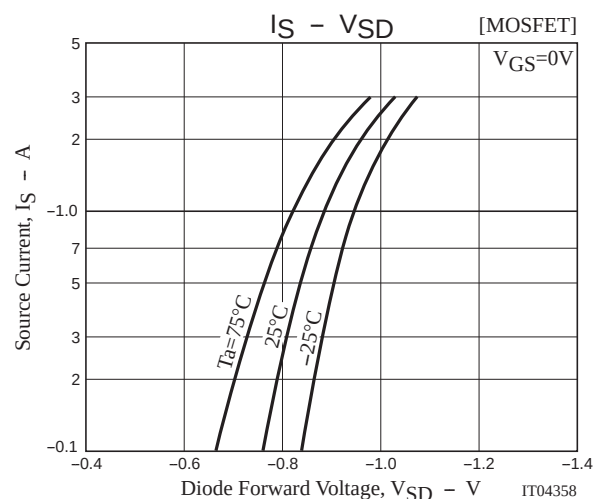
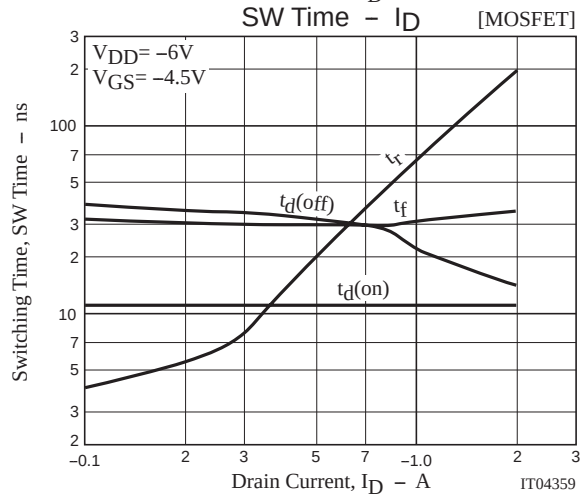
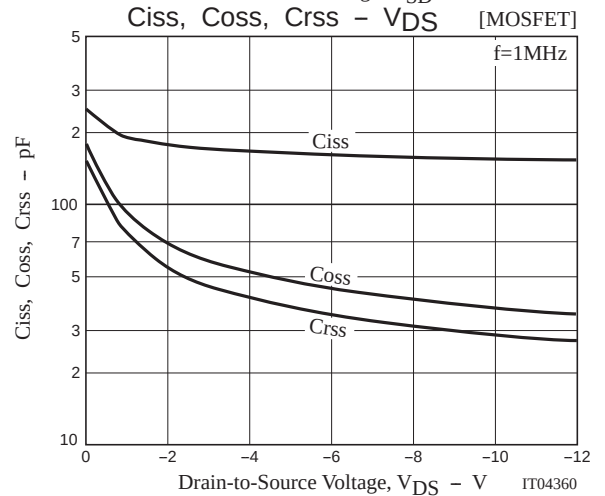
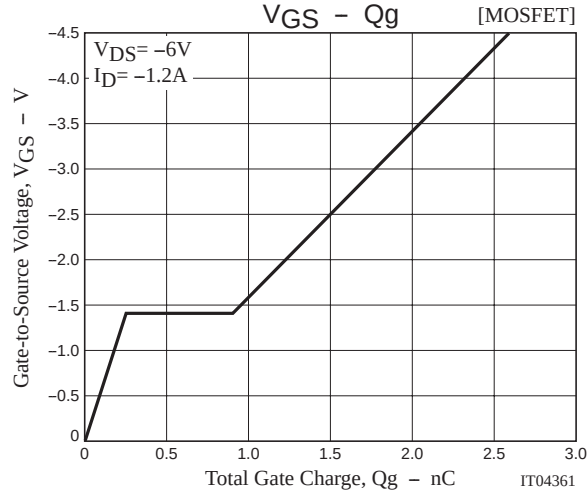
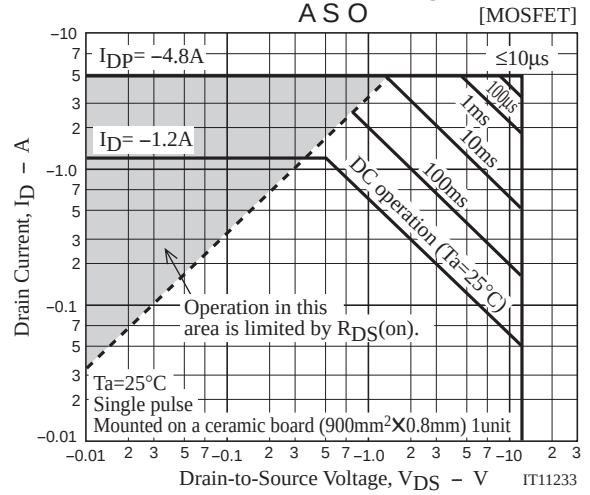
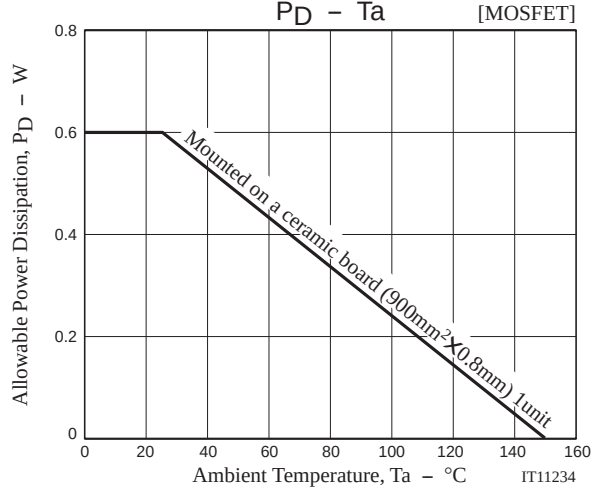
[MOSFET]

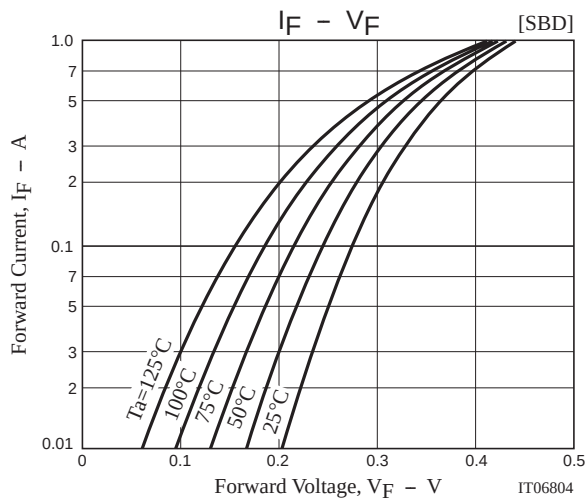
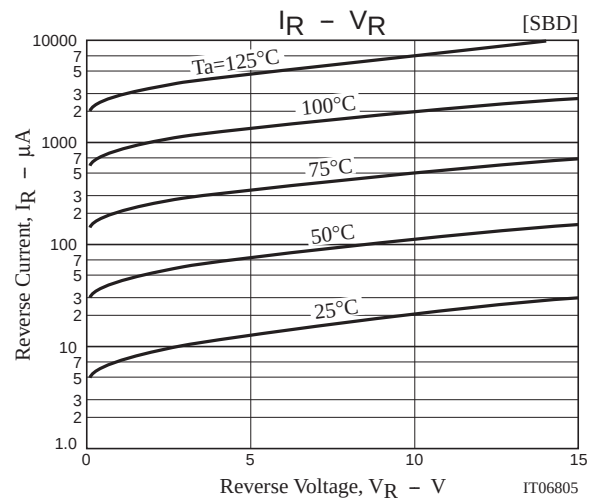
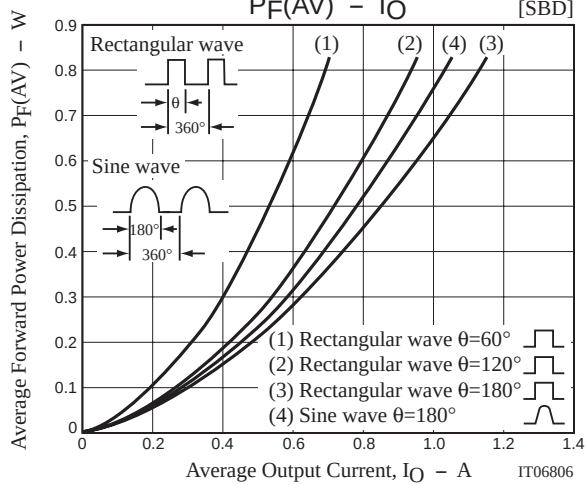
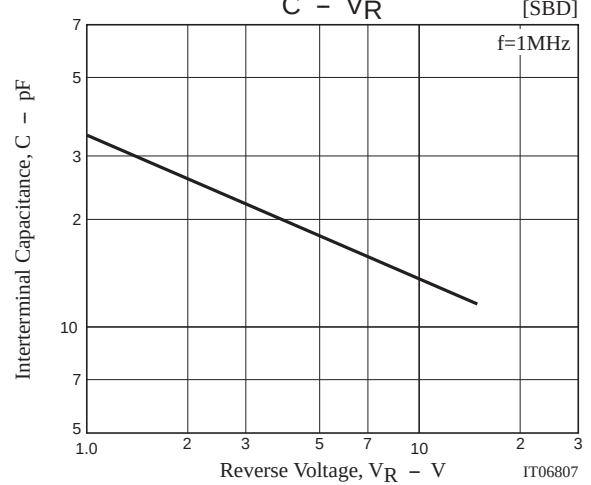
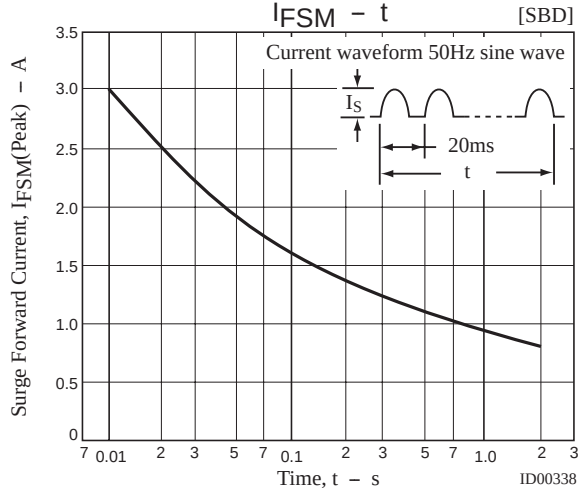


t_{rr} Test Circuit

[SBD]







Note on usage : Since the SCH2809 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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